

## METHOD AND APPARATUS FOR CHEMICAL-MECHANICAL POLISHING AND MANUFACTURE OF SEMICONDUCTOR SUBSTRATE

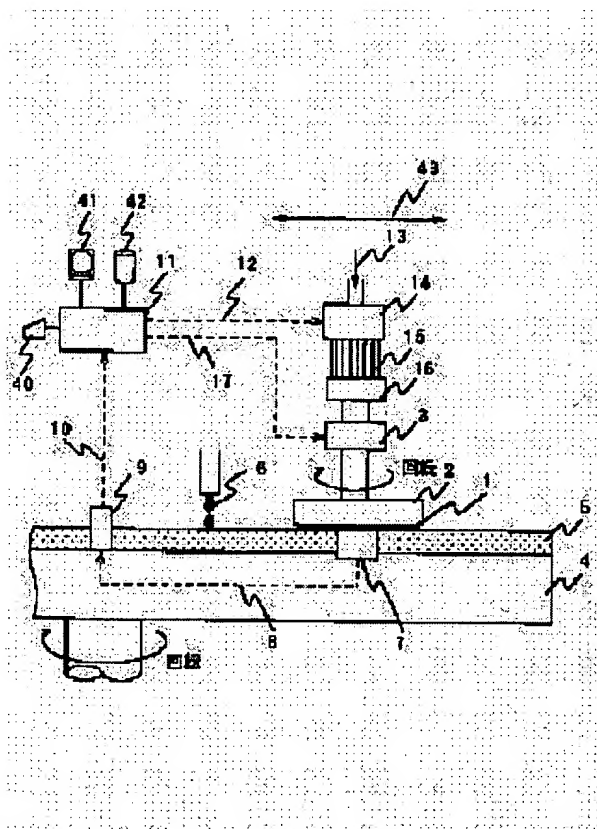
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### Abstract of JP9148284

**PROBLEM TO BE SOLVED:** To make the thickness of the polishing insulating film formed on a board uniform by chemical and mechanical polishing the board surface by controlling the polishing pressures at a plurality of two-dimensional areas in the surface.

**SOLUTION:** A workpiece 1 supported by a chuck 2 is brought into contact with a polishing pad 5 while supplying polishing liquid 6 onto the rotating pad 5. Further, the polishing load is applied to the chuck 2 rotated by a motor 3. It is reciprocating moved relatively to a polishing surface plate 4 in the radial direction of the plate 4. The workpiece 1 is chemically and mechanically polished by adopting both the chemical polishing by the chemical reaction with the alkaline solution contained in the liquid 6 and the mechanical polishing by the abrasive of SiO<sub>2</sub> or the like. Thus, the thickness of an insulating film or metal film can be made uniform and flat.



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